Creation,

Characterization and Applications of Ultrashort Laser Pulses

Eric Mazur Harvard University

NATO Advanced Summer Institute, Erice, Italy Spectroscopy of systems with confined spatial structures 20 June 2001





Outline

linear and nonlinear propagation
 femtosecond measurements
 dynamics of phase transitions

laser-assisted surface etching

Outline

linear and nonlinear propagation femtosecond measurements dynamics of phase transitions laser-assisted surface etching







- time resolution
- high intensity
- nonlinear optics
- new physics

Governed by wave equation

$$\nabla^2 \vec{E} - \frac{\mu \epsilon}{c^2} \frac{\partial^2 \vec{E}}{\partial t^2} = 0$$

Governed by wave equation

$$\nabla^2 \vec{E} - \frac{\mu \epsilon}{c^2} \frac{\partial^2 \vec{E}}{\partial t^2} = 0$$

Solution:
$$\vec{E} = \vec{E}_o e^{i(kx - \omega t)}$$

Governed by wave equation

$$\nabla^2 \vec{E} - \frac{\mu \epsilon}{c^2} \frac{\partial^2 \vec{E}}{\partial t^2} = 0$$

Solution:
$$\vec{E} = \vec{E}_o e^{i(kx - \omega t)}$$

where

$$\frac{\omega}{k} = \frac{1}{\sqrt{\epsilon\mu}} c = \frac{1}{n} c$$

Governed by wave equation

$$\nabla^2 \vec{E} - \frac{\mu \epsilon}{c^2} \frac{\partial^2 \vec{E}}{\partial t^2} = 0$$

Solution:
$$\vec{E} = \vec{E}_o e^{i(kx - \omega t)}$$

where
$$\frac{\omega}{k} = \frac{1}{\sqrt{\epsilon\mu}} c = \frac{1}{n} c$$

In non-ferromagnetic media $\mu \approx 1$, and so $n \approx \sqrt{\epsilon}$. In dispersive media $n = n(\omega)$.









Alternatively, ϵ is measure of the attenuation of the field



Alternatively, ϵ is measure of the attenuation of the field



In vacuum:
$$f\lambda = \frac{\omega}{k} = c \implies \omega = c k$$



In medium:

$$v = \frac{c}{\sqrt{\epsilon(\omega)}} = \frac{c}{n} \qquad \Rightarrow \qquad \omega = \frac{c}{\sqrt{\epsilon}}k$$



Which charges participate?















Bound electrons

Electron on a string:

$$F_{binding} = -m_e \omega_o^2 x$$

Bound electrons

Electron on a string:

$$F_{binding} = -m_e \omega_o^2 x$$
$$F_{damping} = -m_e \gamma \frac{dx}{dt}$$

Bound electrons

Electron on a string:

$$F_{binding} = -m_e \omega_o^2 x$$

$$F_{damping} = -m_e \gamma \frac{dx}{dt}$$

$$F_{driving} = -eE = -eE_o e^{-i\omega t}$$

Electron on a string:

$$F_{binding} = -m_e \omega_o^2 x$$

$$F_{damping} = -m_e \gamma \frac{dx}{dt}$$

$$F_{driving} = -eE = -eE_o e^{-i\omega t}$$

Equation of motion

$$m\frac{d^2x}{dt^2} = \sum F$$

Electron on a string:

$$F_{binding} = -m_e \omega_o^2 x$$

$$F_{damping} = -m_e \gamma \frac{dx}{dt}$$

$$F_{driving} = -eE = -eE_o e^{-i\omega t}$$

Equation of motion

$$m\frac{d^2x}{dt^2} = \sum F$$

$$m\frac{d^2x}{dt^2} + m\gamma\frac{dx}{dt} + m\omega_o^2 x = -eE$$

Steady state: electron oscillates at driving frequency

$$x(t) = x_o e^{-i\omega t}$$
 $x_o = -\frac{e}{m} \frac{1}{(\omega_o^2 - \omega^2) - i\gamma\omega} E_o$

Steady state: electron oscillates at driving frequency

$$x(t) = x_o e^{-i\omega t} \qquad x_o = -\frac{e}{m} \frac{1}{(\omega_o^2 - \omega^2) - i\gamma\omega} E_o$$

Oscillating dipole

$$p(t) = -e x(t) = \frac{e^2}{m} \frac{1}{(\omega_o^2 - \omega^2) - i\gamma\omega} E_o e^{-i\omega t}$$

Steady state: electron oscillates at driving frequency

$$x(t) = x_o e^{-i\omega t} \qquad x_o = -\frac{e}{m} \frac{1}{(\omega_o^2 - \omega^2) - i\gamma\omega} E_o$$

Oscillating dipole

$$p(t) = -e x(t) = \frac{e^2}{m} \frac{1}{(\omega_o^2 - \omega^2) - i\gamma\omega} E_o e^{-i\omega t}$$

Polarization

$$P(t) = \left(\frac{Ne^2}{m}\right) \sum_{j} \frac{f_j}{(\omega_j^2 - \omega^2) - i\gamma_j \omega} E(t) \equiv \epsilon_o \chi_e E(t)$$

$$\boldsymbol{\epsilon}(\boldsymbol{\omega}) \equiv 1 + \chi_e = 1 + \frac{Ne^2}{\boldsymbol{\epsilon}_o m} \sum_{j} \frac{f_j}{(\omega_j^2 - \omega^2) - i\gamma_j \omega}$$
Dielectric function

$$\boldsymbol{\epsilon}(\boldsymbol{\omega}) \equiv 1 + \chi_e = 1 + \frac{Ne^2}{\boldsymbol{\epsilon}_o m} \sum_{j} \frac{f_j}{(\omega_j^2 - \omega^2) - i\gamma_j \omega}$$



Bound electrons

amplitude of bound charge oscillation



Below resonance: bound charges keep up with driving field ⇒ field attenuated, wave propagates more slowly



At resonance: energy transfer from wave to bound charges \Rightarrow wave attenuates (absorption)



Above resonance: bound charges cannot keep up with driving field \Rightarrow dielectric like a vacuum



Dielectric function

$$\boldsymbol{\epsilon}(\boldsymbol{\omega}) \equiv 1 + \chi_e = 1 + \frac{Ne^2}{\boldsymbol{\epsilon}_o m} \sum_{j} \frac{f_j}{(\omega_j^2 - \omega^2) - i\gamma_j \omega}$$



Free electrons

No binding:

$$F_{binding} \approx 0$$

No binding:

$$F_{binding} \approx 0$$

Equation of motion:

$$m\frac{d^2x}{dt^2} + m\gamma\frac{dx}{dt} = -eE$$

No binding:

$$F_{binding} \approx 0$$

Equation of motion:

$$m\frac{d^2x}{dt^2} + m\gamma\frac{dx}{dt} = -eE$$

Solution: $x(t) = \frac{e}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t)$ (no resonance)

No binding:

$$F_{binding} \approx 0$$

Equation of motion:

$$m\frac{d^2x}{dt^2} + m\gamma\frac{dx}{dt} = -eE$$

Solution: $x(t) = \frac{e}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t)$ (no resonance)

Low frequency ($\omega \ll 1$) \Rightarrow current generated

$$J = -Ne \frac{dx}{dt} = \frac{Ne^2}{m} \frac{1}{\gamma - i\omega} E \approx \frac{Ne^2}{m\gamma} E \equiv \sigma E$$

$\omega \gg \gamma$: σ complex \Rightarrow *J* out of phase with *E*

 $\omega \gg \gamma$: σ complex \Rightarrow *J* out of phase with *E* Dipole:

$$p(t) = -e x(t) = -\frac{e^2}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t)$$

 $\omega \gg \gamma$: σ complex $\Rightarrow J$ out of phase with *E* Dipole:

$$p(t) = -e x(t) = -\frac{e^2}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t)$$

Polarization

$$P(t) = -\frac{Ne^2}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t) \equiv \epsilon_o \chi_e E(t)$$

 $\omega \gg \gamma$: σ complex $\Rightarrow J$ out of phase with *E* Dipole:

$$p(t) = -e x(t) = -\frac{e^2}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t)$$

Polarization

$$P(t) = -\frac{Ne^2}{m} \frac{1}{\omega^2 + i\gamma\omega} E(t) \equiv \epsilon_o \chi_e E(t)$$

Dielectric function

$$\epsilon(\omega) \equiv 1 + \chi_e = 1 - \frac{Ne^2}{m\epsilon_o} \frac{1}{\omega^2 + i\gamma\omega} = \epsilon'(\omega) + i\epsilon''(\omega)$$

Plasma

$$\boldsymbol{\gamma} \approx 0 \qquad \Rightarrow \quad \boldsymbol{\epsilon}'' = 0$$

$$\epsilon'(\omega) = 1 - \frac{Ne^2}{m\epsilon_o} \frac{1}{\omega^2} \equiv 1 - \frac{\omega_p^2}{\omega^2}$$



Plasma

Add damping $\gamma \leq \omega_p$



Plasma

Plasma acts like a high-pass filter:













Linear response

$$P(t) = \epsilon_o \chi_e E(t)$$



Linear response $P(t) = \epsilon_o \chi_e E(t)$



Linear response $P(t) = \epsilon_o \chi_e E(t)$



Linear response

$$P(t) = \epsilon_o \chi_e E(t)$$



Nonlinear polarization:

$$P = \chi^{(1)}E + \chi^{(2)}E^2 + \chi^{(3)}E^3 + \dots$$

$$P = P^{(1)} + P^{(2)} + P^{(3)} + \dots$$



E = 0













Р




















In medium with inversion symmetry

$$\vec{P}^{(2)} = \vec{\chi}^{(2)} : \vec{E} \vec{E} \implies - \vec{P}^{(2)} = \vec{\chi}^{(2)} : (-\vec{E})(-\vec{E})$$

In medium with inversion symmetry

$$\vec{P}^{(2)} = \vec{\chi}^{(2)} : \vec{E} \vec{E} \implies - \vec{P}^{(2)} = \vec{\chi}^{(2)} : (-\vec{E})(-\vec{E})$$

and so
$$\chi^{(2)} = -\chi^{(2)} = 0$$

In medium with inversion symmetry

$$\vec{P}^{(2)} = \vec{\chi}^{(2)} : \vec{E} \vec{E} \implies - \vec{P}^{(2)} = \vec{\chi}^{(2)} : (-\vec{E})(-\vec{E})$$

and so
$$\chi^{(2)} = -\chi^{(2)} = 0$$

... but ...



How to reconcile
$$\chi^{(2)} = -\chi^{(2)} = 0$$
 with ?



Nonlinear polarization:

$$P = \chi^{(1)}E + \chi^{(3)}E^3 + \dots$$

Nonlinear polarization:

$$P = \chi^{(1)}E + \chi^{(3)}E^3 + \dots$$

Third order polarization

$$P^{(3)}(t) = \chi^{(3)}E(t)E^{*}(t)E(t) = \chi^{(3)}I(t)E(t)$$

Nonlinear polarization:

$$P = \chi^{(1)}E + \chi^{(3)}E^3 + \dots$$

Third order polarization

$$P^{(3)}(t) = \chi^{(3)}E(t)E^{*}(t)E(t) = \chi^{(3)}I(t)E(t)$$

and so $P = P^{(1)} + P^{(3)} = (\chi^{(1)} + \chi^{(3)}I)E \equiv \chi_{eff}E$

Nonlinear polarization:

$$P = \chi^{(1)}E + \chi^{(3)}E^3 + \dots$$

Third order polarization

$$P^{(3)}(t) = \chi^{(3)}E(t)E^{*}(t)E(t) = \chi^{(3)}I(t)E(t)$$

and so $P = P^{(1)} + P^{(3)} = (\chi^{(1)} + \chi^{(3)}I)E \equiv \chi_{eff}E$

$$n = \sqrt{\epsilon} = \sqrt{1 + \chi_{eff}} \approx \sqrt{1 + \chi^{(1)}} + \frac{1}{2} \frac{\chi^{(3)}I}{\sqrt{1 + \chi^{(1)}}} = n_o + n_2 I$$

$$n = n_o + n_2 I$$



$$n = n_o + n_2 I$$



$$n = n_o + n_2 I$$



$$n = n_o + n_2 I$$



$$n = n_o + n_2 I$$



Phase:

$$\frac{\phi}{2\pi} = \frac{nL}{\lambda}$$

Phase:

$$\frac{\phi}{2\pi} = \frac{nL}{\lambda}$$

$$\phi = \frac{2\pi}{\lambda} L(n_o + n_2 I)$$

Phase:

$$\frac{\phi}{2\pi} = \frac{nL}{\lambda}$$

$$\phi = \frac{2\pi}{\lambda} L(n_o + n_2 I)$$

Frequency change:

$$\Delta \omega = -\frac{d\phi}{dt} = \frac{-2\pi}{\lambda} Ln_2 \frac{dI}{dt}$$

Phase:

$$\frac{\phi}{2\pi} = \frac{nL}{\lambda}$$

$$\phi = \frac{2\pi}{\lambda} L(n_o + n_2 I)$$

Frequency change:

$$\Delta \omega = -\frac{d\phi}{dt} = \frac{-2\pi}{\lambda} Ln_2 \frac{dI}{dt}$$





Spatial intensity profile...



Spatial intensity profile...



...causes self-focusing



Outline

linear and nonlinear propagation
femtosecond measurements
dynamics of phase transitions
laser-assisted surface etching

How to measure on the femtosecond time scale?



Use pump-probe technique



Use pump-probe technique



Use pump-probe technique



Vary delay to get time resolution



Dispersion stretches the pulse



Compensate by rearranging spectral components!







How do these arrangements work?

Does path length difference compensate?



Does path length difference compensate?



Does path length difference compensate?



Grating gives low frequency longer path length...
Does path length difference compensate?



Does path length difference compensate?



Does path length difference compensate?



Does path length difference compensate?



...so prism gives low frequency shorter path length...















So not path length but
$$\frac{d^2\phi}{d\omega^2}$$
 matters!

	$rac{dl_{eff}}{d\omega}$	$rac{d^2\phi}{d\omega^2}$
dispersion	+	+
gratings	-	-
prisms	+	_

Representation of pulses



Spectrum of sinusoidal intensity is a delta function

$$I(t) = \cos^2(\omega_o t) \implies P(\omega) = \delta(\omega - \omega_o)$$

Representation of pulses



Modulate amplitude

$$I(t) = \exp\left[-\frac{t^2}{\sigma_t^2}\right] \cos^2(\omega_o t)$$

$$E(t) = \exp\left[-\frac{t^2}{2\sigma_t^2} - i\omega_o t\right]$$

$$E(t) = \exp\left[-\frac{t^2}{2\sigma_t^2} - i\omega_o t\right]$$

$$E(\omega) = \frac{1}{\sqrt{2\pi}} \int_{-\infty}^{\infty} \exp\left[-\frac{t^2}{2\sigma_t^2} + i(\omega - \omega_o)t\right] dt =$$

$$E(t) = \exp\left[-\frac{t^2}{2\sigma_t^2} - i\omega_o t\right]$$

$$E(\omega) = \frac{1}{\sqrt{2\pi}} \int_{-\infty}^{\infty} \exp\left[-\frac{t^2}{2\sigma_t^2} + i(\omega - \omega_o)t\right] dt =$$

$$=\frac{1}{\sqrt{2\pi}}\exp\left[-\frac{\sigma_t^2(\omega-\omega_o)^2}{2}\right]\int_{-\infty}^{\infty}\exp\left[\frac{t}{\sqrt{2}\sigma_t}-i\frac{(\omega-\omega_o)\sigma_t}{\sqrt{2}}\right]^2dt=$$

$$E(t) = \exp\left[-\frac{t^2}{2\sigma_t^2} - i\omega_o t\right]$$

$$E(\omega) = \frac{1}{\sqrt{2\pi}} \int_{-\infty}^{\infty} \exp\left[-\frac{t^2}{2\sigma_t^2} + i(\omega - \omega_o)t\right] dt =$$

$$= \frac{1}{\sqrt{2\pi}} \exp\left[-\frac{\sigma_t^2(\omega - \omega_o)^2}{2}\right] \int_{-\infty}^{\infty} \exp\left[\frac{t}{\sqrt{2\sigma_t}} - i\frac{(\omega - \omega_o)\sigma_t}{\sqrt{2}}\right]^2 dt =$$

$$= \sigma_t \exp\left[-\frac{\sigma_t^2(\omega - \omega_o)^2}{2}\right] \equiv \sigma_t \exp\left[-\frac{(\omega - \omega_o)^2}{2\sigma_\omega^2}\right]$$

Representation of pulses



Pulse duration-bandwidth product: $\sigma_t \sigma_\omega = 1$

$$I(t) = [\operatorname{Re} E(t)]^2 \propto \exp\left[-\frac{t^2}{\sigma_t^2}\right] \cos^2(\omega_o t)$$

$$P(\omega) = E(\omega)E^*(\omega) = \exp\left[-\frac{(\omega-\omega_o)^2}{\sigma_{\omega}^2}\right]$$

Representation of pulses



Pulse duration-bandwidth product: $\sigma_t \sigma_{\omega} = 1$

$$I(t) = [\operatorname{Re} E(t)]^2 \propto \exp\left[-\frac{t^2}{\sigma_t^2}\right] \cos^2(\omega_o t)$$

$$P(\omega) = E(\omega)E^*(\omega) = \exp\left[-\frac{(\omega - \omega_o)^2}{\sigma_{\omega}^2}\right]$$

Wigner representation:

$$W(t,\omega) = \frac{1}{2\pi} \int_{-\infty}^{\infty} E\left(\omega + \frac{\omega'}{2}\right) E^*\left(\omega - \frac{\omega'}{2}\right) e^{-i\omega't} d\omega' =$$

$$= \int_{-\infty}^{\infty} E\left(t + \frac{t'}{2}\right) E^*\left(t - \frac{t'}{2}\right) e^{-i\omega t'} dt'$$

Wigner representation:

$$W(t,\omega) = \frac{1}{2\pi} \int_{-\infty}^{\infty} E\left(\omega + \frac{\omega'}{2}\right) E^*\left(\omega - \frac{\omega'}{2}\right) e^{-i\omega't} d\omega' =$$

$$= \int_{-\infty}^{\infty} E\left(t + \frac{t'}{2}\right) E^*\left(t - \frac{t'}{2}\right) e^{-i\omega t'} dt'$$

$$\frac{1}{2\pi}\int_{-\infty}^{\infty} W(t,\omega) \ d\omega = |E(t)|^2 = I(t)$$

Wigner representation:

$$W(t,\omega) = \frac{1}{2\pi} \int_{-\infty}^{\infty} E\left(\omega + \frac{\omega'}{2}\right) E^*\left(\omega - \frac{\omega'}{2}\right) e^{-i\omega't} d\omega' =$$

$$= \int_{-\infty}^{\infty} E\left(t + \frac{t'}{2}\right) E^*\left(t - \frac{t'}{2}\right) e^{-i\omega t'} dt'$$

$$\frac{1}{2\pi}\int_{-\infty}^{\infty} W(t,\omega) \ d\omega = |E(t)|^2 = I(t)$$

$$\int_{-\infty}^{\infty} W(t,\omega) dt = |E(\omega)|^2 = I(\omega)$$

Joint time-frequency representation

Energy:

$$\frac{1}{2\pi}\int_{-\infty}^{\infty}\int_{-\infty}^{\infty}W(t,\omega)\ dt\ d\omega$$



Joint time-frequency representation

Energy:

$$\frac{1}{2\pi}\int_{-\infty}^{\infty}\int_{-\infty}^{\infty}W(t,\omega)\ dt\ d\omega$$



 $W(t,\omega)$ must be nonzero in phase-space area larger than π

Joint time-frequency representation

Energy:

$$\frac{1}{2\pi}\int_{-\infty}^{\infty}\int_{-\infty}^{\infty}W(t,\omega)\ dt\ d\omega$$



 $W(t,\omega)$ must be nonzero in phase-space area larger than π

Use pulse to measure itself...



Use pulse to measure itself...



Use pulse to measure itself...



Electric field at SHG crystal

$$E_{tot}(t,\tau) = \frac{1}{\sqrt{2}}E_1(t) + \frac{1}{\sqrt{2}}E_2(t+\tau)$$

Electric field at SHG crystal

$$E_{tot}(t,\tau) = \frac{1}{\sqrt{2}}E_1(t) + \frac{1}{\sqrt{2}}E_2(t+\tau)$$

Second harmonic field

$$E_{2\omega} \propto \chi^{(2)} E_{tot}^2$$

Electric field at SHG crystal

$$E_{tot}(t,\tau) = \frac{1}{\sqrt{2}}E_1(t) + \frac{1}{\sqrt{2}}E_2(t+\tau)$$

Second harmonic field

$$E_{2\omega} \propto \chi^{(2)} E_{tot}^2$$

Second harmonic intensity

 $I_{2\omega}(t,\tau) \propto |\chi^{(2)}|^2 |E_{tot}^2|^2 = |\chi^{(2)}|^2 |E_1^2(t) + 2E_1(t)E_2(t+\tau) + E_2^2(t+\tau)|^2$



Second harmonic intensity

 $I_{2\omega}(t,\tau) \propto |\chi^{(2)}|^2 |E_{tot}^2|^2 = |\chi^{(2)}|^2 |E_1^2(t) + 2E_1(t)E_2(t+\tau) + E_2^2(t+\tau)|^2$

detector selects middle term

Integrated detector signal yields intensity autocorrelation

$$A(\tau) = \int I_{2\omega}(t,\tau) dt \propto \int |\chi^{(2)}|^2 4 |E_1(t)|^2 |E_2(t+\tau)|^2 dt$$

Integrated detector signal yields intensity autocorrelation

$$A(\tau) = \int I_{2\omega}(t,\tau) dt \propto \int |\chi^{(2)}|^2 4 |E_1(t)|^2 |E_2(t+\tau)|^2 dt$$
$$A(\tau) \propto \int I_1(t) I_2(t+\tau) dt$$

Integrated detector signal yields intensity autocorrelation

$$A(\tau) = \int I_{2\omega}(t,\tau) dt \propto \int |\chi^{(2)}|^2 4 |E_1(t)|^2 |E_2(t+\tau)|^2 dt$$
$$A(\tau) \propto \int I_1(t) I_2(t+\tau) dt$$


Integrated detector signal yields intensity autocorrelation

$$A(\tau) = \int I_{2\omega}(t,\tau) dt \propto \int |\chi^{(2)}|^2 4 |E_1(t)|^2 |E_2(t+\tau)|^2 dt$$
$$A(\tau) \propto \int I_1(t) I_2(t+\tau) dt$$



Alternative colinear geometry































 $I_{2\omega}(t,\tau) \propto |\chi^{(2)}|^2 |E_{tot}^2|^2 = |\chi^{(2)}|^2 |E_1^2(t) + 2E_1(t)E_2(t+\tau) + E_2^2(t+\tau)|^2$

at $\tau = 0$: $I_{2\omega}(t,\tau) \propto 16E^4(t)$



 $I_{2\omega}(t,\tau) \propto |\chi^{(2)}|^2 |E_{tot}^2|^2 = |\chi^{(2)}|^2 |E_1^2(t) + 2E_1(t)E_2(t+\tau) + E_2^2(t+\tau)|^2$

at
$$\tau = 0$$
: $I_{2\omega}(t,\tau) \propto 16E^4(t)$

as $\tau \to \pm \infty$:

$$I_{2\omega}(t,\tau) \propto 2E^4(t)$$



 $I_{2\omega}(t,\tau) \propto |\chi^{(2)}|^2 |E_{tot}^2|^2 = |\chi^{(2)}|^2 |E_1^2(t) + 2E_1(t)E_2(t+\tau) + E_2^2(t+\tau)|^2$

at
$$\tau = 0$$
: $I_{2\omega}(t,\tau) \propto 16E^4(t)$

as $\tau \to \pm \infty$:

$$I_{2\omega}(t,\tau) \propto 2E^4(t)$$



Do we really need the second-harmonic crystal...?



Would this work?



Intensity at detector

$$I_{\omega}(t,\tau) \propto |E_1(t) + E_2(t+\tau)|^2$$

Intensity at detector

$$I_{\omega}(t,\tau) \propto |E_1(t) + E_2(t+\tau)|^2$$

Detected signal

$$S_{\omega}(\tau) = \int I_{\omega}(t,\tau) dt$$

Intensity at detector

$$I_{\omega}(t,\tau) \propto |E_1(t) + E_2(t+\tau)|^2$$

Detected signal

$$S_{\omega}(\tau) = \int I_{\omega}(t,\tau) dt$$

SO

$$S_{\omega}(\tau) \propto \int \{ |E_1(t)|^2 + |E_2(t+\tau)|^2 + E_1(t)E_2^*(t+\tau) + E_1^*(t)E_2(t+\tau) \} dt$$









But what about dispersion?














Let
$$E_{disp}(\omega) = E_{orig}(\omega)e^{-i\phi(\omega)}$$
.

Let $E_{disp}(\omega) = E_{orig}(\omega)e^{-i\phi(\omega)}$. Convolution theorem $f_1(t) \otimes f_2(t) \equiv \int f_1(t+\tau)f_2^*(t) dt = \mathcal{F}^{-1}\{f_1(\omega)f_2^*(\omega)\}$

Let
$$E_{disp}(\omega) = E_{orig}(\omega)e^{-i\phi(\omega)}$$
. Convolution theorem
 $f_1(t) \otimes f_2(t) \equiv \int f_1(t+\tau)f_2^*(t) dt = \mathcal{F}^{-1}\{f_1(\omega)f_2^*(\omega)\}$

Interference term in linear autocorrelation:

$$\int E_{disp}(t+\tau)E_{disp}^{*}(t) dt = \mathcal{F}^{-1}\{E_{disp}(\omega)E_{disp}^{*}(\omega)\} =$$

Let
$$E_{disp}(\omega) = E_{orig}(\omega)e^{-i\phi(\omega)}$$
. Convolution theorem
 $f_1(t) \otimes f_2(t) \equiv \int f_1(t+\tau)f_2^*(t) dt = \mathcal{F}^{-1}\{f_1(\omega)f_2^*(\omega)\}$

Interference term in linear autocorrelation:

$$\int E_{disp}(t+\tau)E_{disp}^{*}(t) dt = \mathcal{F}^{-1}\{E_{disp}(\omega)E_{disp}^{*}(\omega)\} =$$

$$= \mathscr{F}^{-1} \{ E_{orig}(\omega) e^{i\phi(\omega)} E_{orig}^{*}(\omega) e^{-i\phi(\omega)} \} =$$

Let
$$E_{disp}(\omega) = E_{orig}(\omega)e^{-i\phi(\omega)}$$
. Convolution theorem
 $f_1(t) \otimes f_2(t) \equiv \int f_1(t+\tau)f_2^*(t) dt = \mathcal{F}^{-1}\{f_1(\omega)f_2^*(\omega)\}$

Interference term in linear autocorrelation:

$$\int E_{disp}(t+\tau)E_{disp}^{*}(t) dt = \mathcal{F}^{-1}\{E_{disp}(\omega)E_{disp}^{*}(\omega)\} =$$

$$= \mathscr{F}^{-1} \{ E_{orig}(\omega) e^{i\phi(\omega)} E_{orig}^{*}(\omega) e^{-i\phi(\omega)} \} =$$

$$= \mathscr{F}^{-1}\{E_{orig}(\omega)E_{orig}^{*}(\omega)\} = \int E_{orig}(t+\tau) E_{orig}^{*}(t) dt$$



IRG ("instantaneous response gate"): device whose transmittance of a weak probe pulse is proportional to the intensity envelope of the pump ("gate")

T(t) = u(t)



Transmitted intensity

$$I(t) = I_o T(t) = I_o u(t) = I_o \exp\left[-\frac{t^2}{\sigma_t^2}\right]$$



Transmitted intensity

$$I(t) = I_o T(t) = I_o u(t) = I_o \exp\left[-\frac{t^2}{\sigma_t^2}\right]$$
$$\sigma_t \sigma_\omega = 1$$



Transmitted intensity

$$I(t,\tau) = u(t)r(t+\tau) = \exp\left[-\frac{t^2}{\sigma^2}\right] \exp\left[-\left(\frac{t+\tau}{\sigma}\right)^2\right] =$$
$$= \exp\left[-\frac{2t^2 + 2t\tau + \tau^2}{\sigma^2}\right] = \exp\left[-\frac{2t^2 + 2t\tau + \tau^2/2}{\sigma^2}\right] \exp\left[-\frac{\tau^2}{2\sigma^2}\right] =$$



Transmitted intensity

$$I(t,\tau) = \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-\left(\frac{t+\tau/2}{\sigma/\sqrt{2}}\right)^2\right]$$

so $I(t,\tau)$ narrowed by $\sqrt{2}$



$$S(\tau) = \int_{-\infty}^{\infty} I(t,\tau) dt = \int_{-\infty}^{\infty} \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-2\left(\frac{t+\tau/2}{\sigma^2}\right)^2\right] dt$$



$$S(\tau) = \int_{-\infty}^{\infty} I(t,\tau) dt = \int_{-\infty}^{\infty} \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-2\left(\frac{t+\tau/2}{\sigma^2}\right)^2\right] dt$$



$$S(\tau) = \int_{-\infty}^{\infty} I(t,\tau) dt = \int_{-\infty}^{\infty} \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-2\left(\frac{t+\tau/2}{\sigma^2}\right)^2\right] dt$$



$$S(\tau) = \int_{-\infty}^{\infty} I(t,\tau) dt = \int_{-\infty}^{\infty} \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-2\left(\frac{t+\tau/2}{\sigma^2}\right)^2\right] dt$$
$$= \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \int_{-\infty}^{\infty} \exp\left[-\frac{2u^2}{\sigma^2}\right] du = \sqrt{\frac{\pi}{2}} \sigma \exp\left[-\frac{\tau^2}{(\sigma\sqrt{2})^2}\right]$$



$$S(\tau) = \int_{-\infty}^{\infty} I(t,\tau) dt = \int_{-\infty}^{\infty} \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \exp\left[-2\left(\frac{t+\tau/2}{\sigma^2}\right)^2\right] dt$$
$$= \exp\left[-\frac{\tau^2}{2\sigma^2}\right] \int_{-\infty}^{\infty} \exp\left[-\frac{2u^2}{\sigma^2}\right] du = \sqrt{\frac{\pi}{2}} \sigma \exp\left[-\frac{\tau^2}{(\sigma\sqrt{2})^2}\right]$$



If gate and probe unequal:

$$\sigma_{prod}^{2} = \frac{\sigma_{1}^{2}\sigma_{2}^{2}}{\sigma_{1}^{2} + \sigma_{2}^{2}}$$
 (narrower than both)
$$\sigma_{cc}^{2} = \sigma_{1}^{2} + \sigma_{2}^{2}$$
 (wider than both)



Transmitted field:

$$E_{trans}(t,\tau) \propto \chi^{(3)} E_{probe}(t) |E_{gate}(t+\tau)|^2$$











R. Trebino, et al., Rev. Sci. Instrum. 68, 3277 (1997)



What are the resolution limits?























Outline

linear and nonlinear propagation
femtosecond measurements
dynamics of phase transitions

laser-assisted surface etching
how do femtosecond laser pulses alter a solid?



photons excite valence electrons...



...and create free electrons...



... causing electronic and structural changes...



...which we measure with another pulse





structure



























DUDNTRONIX

Results

2

-

0

0

Conclusions













Results: c-GaAs

DURNTRONIX

Conclusions

10

0

0














































short time scale



short time scale





dielectric function







short time scale

Х

structure



4 2 (A) 0 2 -2 -2

Г momentum

-4

bandstructure





short time scale

structure



dielectric function







short time scale

structure



oto

Г momentum Х

4

energy (eV) c 0 c

-4

*E*₁

bandstructure





short time scale

structure



bandstructure







short time scale

structure dielectric function bandstructure 40 4 0.70 *F_{th}* GaAs 30 dielectric function energy (eV) k 0 c 20 Ga 10 As 0 -10 _20∟ 0.0 -4 2.0 4.0 photon energy (eV) Х 6.0 Γ momentum

short time scale



D.H. Kim, et al., Sol. State Comm. 89, 119 (1994)

short time scale



electronic effects dominate at short time scales...

short time scale



...but they are not as simple as we used to think

long time scale, high fluence



long time scale, high fluence



gradual drop in gap \rightarrow not electronic effect

Method

Results: a-GaAs

DURNTRONIX

Conclusions

10

0

0






















matches disordered c-GaAs



















Drude-like after 2 ps



plasma frequency decreases



plasma frequency decreases



Results: GeSb

Method

10

0

0

DURNTRONIX

Conclusions






















































Drude-like after 1 ps



plasma frequency decreases



plasma frequency decreases







laser-induced recrystallization



Universal features:

semiconductor-to-metal transition

- semiconductor-to-metal transition
- decrease in bonding-antibonding splitting takes picoseconds

- semiconductor-to-metal transition
- decrease in bonding-antibonding splitting takes picoseconds
- plasma frequency decreases with time

- semiconductor-to-metal transition
- decrease in bonding-antibonding splitting takes picoseconds
- plasma frequency decreases with time
- plasma frequency decreases with increasing fluence

Method

10

0

0

Results: Tellurium

DURNTRONIX

Conclusions

Why Tellurium?

- semimetal (0.3 eV bandgap)
- large ΔR due to A_1 phonons
- A_1 phonons at 3.6 THz

Why Tellurium?

- semimetal (0.3 eV bandgap)
- large ΔR due to A_1 phonons
- A₁ phonons at 3.6 THz

... but A_1 -mode is not IR-active





excitation weakens binding force



ion moves to new equilibrium position



oscillation damps out as force is restored













 A_1 mode



P. Tangney (Princeton) and S. Fahey (Cork), private communication



P. Tangney (Princeton) and S. Fahey (Cork), private communication



P. Tangney (Princeton) and S. Fahey (Cork), private communication










Results



MethodResults

10

0

0

Conclusions

DURNTRONIX

Conclusions

- Femtosecond time-resolved ellipsometry powerful tool for tracking ultrafast electron and lattice dynamics in highly excited solids
- Strong electronic excitation can drive a structural transition
- Direct observation of coherent phonons

Outline

linear and nonlinear propagation
femtosecond measurements
dynamics of phase transitions

laser-assisted surface etching



irradiate with 100-fs 10 kJ/m² pulses



"black silicon"









Discussion

160 Fatal D ×2000 #3548 512 × 480 15mm 20PW -10kV 0000











































absorptance



C. Wu, et al., Appl. Phys. Lett. 78, 1850 (2001)

absorptance



C. Wu, et al., Appl. Phys. Lett. 78, 1850 (2001)

absorptance



C. Wu, et al., Appl. Phys. Lett. 78, 1850 (2001)

Points to keep in mind:

- one-step, maskless process
- large area with uniform high density of spikes
- band structure change






















R.H. Fowler and L. Nordheim, Proc. R. Soc. Lond. A (1928)

<u>Ninda da dan bilada da dan bilada da dan bilada da dan bilada da dan bi</u>

Viele de des teil de de des teils de des teils de des teils de des teils

gold coating



	anode		
الغا حمارها مأليا	in de lan bilain de lan bilain de lan bilain de lan b		
gold coa	ting		







turn-on field (1 µA/cm²): 1.3 V/µm



threshold field (10 µA/cm²): 2.15 V/µm



















Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)









Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)



Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)



Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)



Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)



Y.Y. Lau et al., Phys. Plasmas 1, 2082 (1994)


Space charge effect



Space charge effect







► Results



Ion channeling and electron backscattering

- spikes retain crystalline order
- high density of defects

Secondary ion mass spectrometry:

- ▶ 10²⁰ cm⁻³ sulfur
- ▶ 10¹⁷ cm⁻³ fluorine



sulfur introduces states in the gap



sulfur introduces states in the gap



Janzén, et al., Phys. Rev. B 29,1907 (1984)

states broaden into a band





sulfur band provides additional electrons





Microstructured silicon

fabricated by simple, maskless process



Microstructured silicon

fabricated by simple, maskless process

can be integrated with microelectronics

Summary

Microstructured silicon

fabricated by simple, maskless process

can be integrated with microelectronics

provides stable, high field-emission current

Summary

Microstructured silicon

fabricated by simple, maskless process

can be integrated with microelectronics

provides stable, high field-emission current

▶ is durable













Funding: National Science Foundation US Department of Energy Army Research Office

> Acknowledgments: Prof. N. Bloembergen Prof. H. Ehrenreich Prof. T. Kaxiras

For a copy of this talk and additional information, see:

http://mazur-www.harvard.edu